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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded - Microcontrollers</u>"

Details	
Product Status	Discontinued at Digi-Key
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I ² C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	64
Program Memory Size	384KB (384K x 8)
Program Memory Type	FLASH
EEPROM Size	8K x 8
RAM Size	24K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 17x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	80-LQFP
Supplier Device Package	80-LFQFP (12x12)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f100mkafb-v0

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

Table 1-1. List of Ordering Part Numbers

(1/12)

Pin	Package	Data	Fields of	Ordering Part Number
count	-	flash	Application Note	
20 pins	20-pin plastic LSSOP	Mounted	Α	R5F1006AASP#V0, R5F1006CASP#V0, R5F1006DASP#V0,
	(7.62 mm (300), 0.65			R5F1006EASP#V0
	mm pitch)			R5F1006AASP#X0, R5F1006CASP#X0, R5F1006DASP#X0,
				R5F1006EASP#X0
			D	R5F1006ADSP#V0, R5F1006CDSP#V0, R5F1006DDSP#V0,
				R5F1006EDSP#V0
				R5F1006ADSP#X0, R5F1006CDSP#X0, R5F1006DDSP#X0,
				R5F1006EDSP#X0
			G	R5F1006AGSP#V0, R5F1006CGSP#V0, R5F1006DGSP#V0,
				R5F1006EGSP#V0
				R5F1006AGSP#X0, R5F1006CGSP#X0, R5F1006DGSP#X0,
				R5F1006EGSP#X0
		Not	Α	R5F1016AASP#V0, R5F1016CASP#V0, R5F1016DASP#V0,
		mounted		R5F1016EASP#V0
				R5F1016AASP#X0, R5F1016CASP#X0, R5F1016DASP#X0,
				R5F1016EASP#X0
			D	R5F1016ADSP#V0, R5F1016CDSP#V0, R5F1016DDSP#V0,
				R5F1016EDSP#V0
				R5F1016ADSP#X0, R5F1016CDSP#X0, R5F1016DDSP#X0,
				R5F1016EDSP#X0
24 pins	24-pin plastic	Mounted	Α	R5F1007AANA#U0, R5F1007CANA#U0, R5F1007DANA#U0,
	HWQFN (4 × 4mm,			R5F1007EANA#U0
	0.5 mm pitch)			R5F1007AANA#W0, R5F1007CANA#W0, R5F1007DANA#W0,
				R5F1007EANA#W0
			D	R5F1007ADNA#U0, R5F1007CDNA#U0, R5F1007DDNA#U0,
				R5F1007EDNA#U0
				R5F1007ADNA#W0, R5F1007CDNA#W0, R5F1007DDNA#W0,
			G	R5F1007EDNA#W0 R5F1007AGNA#U0, R5F1007CGNA#U0, R5F1007DGNA#U0,
			G	R5F1007AGNA#00, R5F1007CGNA#00, R5F1007DGNA#00,
				R5F1007AGNA#W0, R5F1007CGNA#W0, R5F1007DGNA#W0,
				R5F1007EGNA#W0
		Not	Α	R5F1017AANA#U0, R5F1017CANA#U0, R5F1017DANA#U0.
		mounted		R5F1017EANA#U0
		mounted		R5F1017AANA#W0, R5F1017CANA#W0, R5F1017DANA#W0,
				R5F1017EANA#W0
			D	R5F1017ADNA#U0, R5F1017CDNA#U0, R5F1017DDNA#U0,
				R5F1017EDNA#U0
				R5F1017ADNA#W0, R5F1017CDNA#W0, R5F1017DDNA#W0,
				R5F1017EDNA#W0

Note For the fields of application, refer to Figure 1-1 Part Number, Memory Size, and Package of RL78/G13.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.



Table 1-1. List of Ordering Part Numbers

(7/12)

Pin count	Package	Data flash	Fields of Application	Ordering Part Number
52 pins	52-pin plastic	Mounted	Α	R5F100JCAFA#V0, R5F100JDAFA#V0, R5F100JEAFA#V0,
	LQFP (10 × 10			R5F100JFAFA#V0, R5F100JGAFA#V0, R5F100JHAFA#V0,
	mm, 0.65 mm			R5F100JJAFA#V0, R5F100JKAFA#V0, R5F100JLAFA#V0
	pitch)			R5F100JCAFA#X0, R5F100JDAFA#X0, R5F100JEAFA#X0,
				R5F100JFAFA#X0, R5F100JGAFA#X0, R5F100JHAFA#X0,
				R5F100JJAFA#X0, R5F100JKAFA#X0, R5F100JLAFA#X0
			D	R5F100JCDFA#V0, R5F100JDDFA#V0, R5F100JEDFA#V0,
				R5F100JFDFA#V0, R5F100JGDFA#V0, R5F100JHDFA#V0,
				R5F100JJDFA#V0, R5F100JKDFA#V0, R5F100JLDFA#V0
				R5F100JCDFA#X0, R5F100JDDFA#X0, R5F100JEDFA#X0,
				R5F100JFDFA#X0, R5F100JGDFA#X0, R5F100JHDFA#X0,
				R5F100JJDFA#X0, R5F100JKDFA#X0, R5F100JLDFA#X0
			G	R5F100JCGFA#V0, R5F100JDGFA#V0, R5F100JEGFA#V0,
				R5F100JFGFA#V0,R5F100JGGFA#V0, R5F100JHGFA#V0,
				R5F100JJGFA#V0
				R5F100JCGFA#X0, R5F100JDGFA#X0, R5F100JEGFA#X0,
				R5F100JFGFA#X0,R5F100JGGFA#X0, R5F100JHGFA#X0,
				R5F100JJGFA#X0
		Not	Α	R5F101JCAFA#V0, R5F101JDAFA#V0, R5F101JEAFA#V0,
		mounted		R5F101JFAFA#V0, R5F101JGAFA#V0, R5F101JHAFA#V0,
				R5F101JJAFA#V0, R5F101JKAFA#V0, R5F101JLAFA#V0
				R5F101JCAFA#X0, R5F101JDAFA#X0, R5F101JEAFA#X0,
				R5F101JFAFA#X0, R5F101JGAFA#X0, R5F101JHAFA#X0,
				R5F101JJAFA#X0, R5F101JKAFA#X0, R5F101JLAFA#X0
			D	R5F101JCDFA#V0, R5F101JDDFA#V0, R5F101JEDFA#V0,
				R5F101JFDFA#V0, R5F101JGDFA#V0, R5F101JHDFA#V0,
				R5F101JJDFA#V0, R5F101JKDFA#V0, R5F101JLDFA#V0
				R5F101JCDFA#X0, R5F101JDDFA#X0, R5F101JEDFA#X0,
				R5F101JFDFA#X0, R5F101JGDFA#X0, R5F101JHDFA#X0,
				R5F101JJDFA#X0, R5F101JKDFA#X0, R5F101JLDFA#X0

Note For the fields of application, refer to Figure 1-1 Part Number, Memory Size, and Package of RL78/G13.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.

Table 1-1. List of Ordering Part Numbers

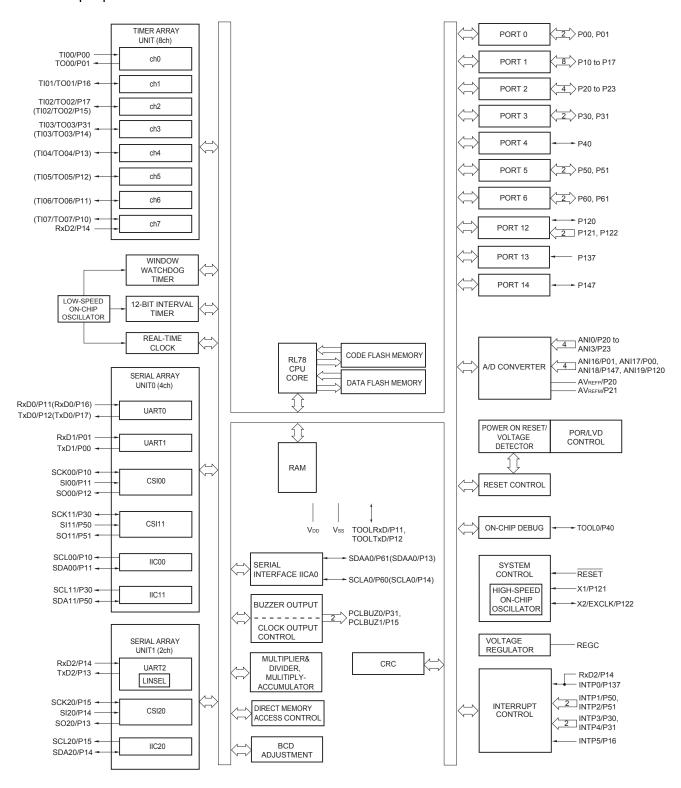
(12/12)

Pin count	Package	Data flash	Fields of Application Note	Ordering Part Number
128 pins	128-pin plastic LFQFP (14 × 20 mm, 0.5 mm pitch)	Mounted	A D	R5F100SHAFB#V0, R5F100SJAFB#V0, R5F100SKAFB#V0, R5F100SLAFB#V0 R5F100SHAFB#X0, R5F100SJAFB#X0, R5F100SKAFB#X0, R5F100SLAFB#X0 R5F100SHDFB#V0, R5F100SJDFB#V0, R5F100SKDFB#V0, R5F100SLDFB#V0 R5F100SHDFB#X0, R5F100SJDFB#X0, R5F100SKDFB#X0, R5F100SLDFB#X0
		Not mounted	A D	R5F101SHAFB#V0, R5F101SJAFB#V0, R5F101SKAFB#V0, R5F101SLAFB#V0 R5F101SHAFB#X0, R5F101SJAFB#X0, R5F101SKAFB#X0, R5F101SLAFB#X0 R5F101SHDFB#V0, R5F101SJDFB#V0, R5F101SKDFB#V0, R5F101SLDFB#V0 R5F101SHDFB#X0, R5F101SJDFB#X0, R5F101SKDFB#X0, R5F101SLDFB#X0

Note For the fields of application, refer to Figure 1-1 Part Number, Memory Size, and Package of RL78/G13.

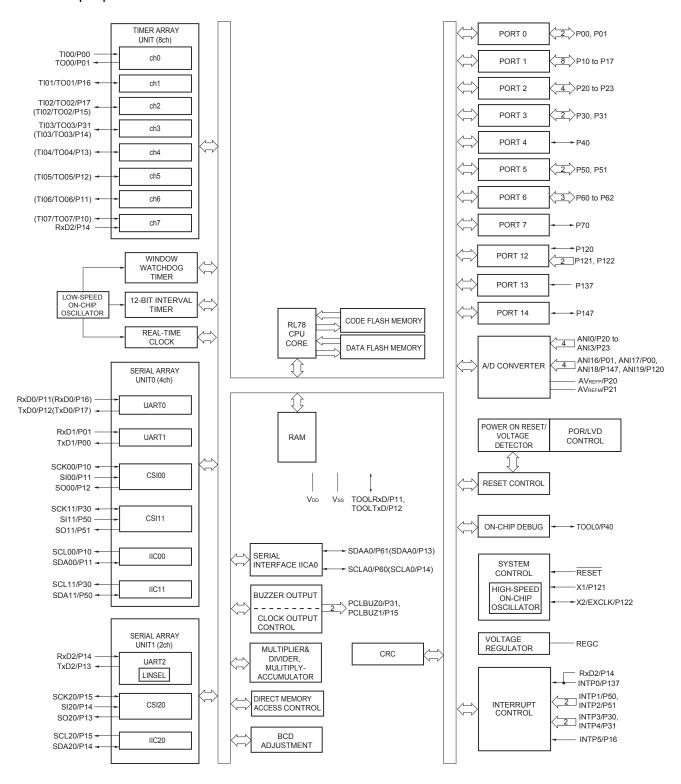
Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.

1.5.4 30-pin products



Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G13 User's Manual.

1.5.5 32-pin products



Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G13 User's Manual.

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V}) (4/5)$

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output voltage, high	V _{OH1}	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ Iон1 = -10.0 mA	EV _{DD0} –			V
		to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to	$4.0 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V},$ $I_{\text{OH1}} = -3.0 \text{ mA}$	EV _{DD0} – 0.7			V
		P117, P120, P125 to P127, P130, P140 to P147	$2.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ loh1 = -2.0 mA	EV _{DD0} – 0.6			V
			1.8 V \leq EV _{DD0} \leq 5.5 V, Іон1 = -1.5 mA	EV _{DD0} – 0.5			V
			$1.6 \text{ V} \le \text{EV}_{\text{DD0}} < 5.5 \text{ V},$ Iон1 = -1.0 mA	EV _{DD0} – 0.5			V
	V _{OH2}	P20 to P27, P150 to P156	1.6 V \leq V _{DD} \leq 5.5 V, I _{OH2} = $-100~\mu$ A	V _{DD} – 0.5			V
Output voltage, low	V _{OL1}	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64	$4.0~V \leq EV_{DD0} \leq 5.5~V,$ $I_{OL1} = 20~mA$			1.3	V
		to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to	$4.0~V \leq EV_{DD0} \leq 5.5~V,$ $I_{OL1} = 8.5~mA$			0.7	V
		P117, P120, P125 to P127, P130, P140 to P147	$2.7~V \leq EV_{\text{DD0}} \leq 5.5~V,$ $I_{\text{OL1}} = 3.0~\text{mA}$			0.6	V
			$2.7~V \leq EV_{\text{DD0}} \leq 5.5~V,$ $I_{\text{OL1}} = 1.5~\text{mA}$			0.4	V
			$1.8~V \leq EV_{DD0} \leq 5.5~V,$ $I_{OL1} = 0.6~mA$			0.4	V
			$1.6 \text{ V} \le \text{EV}_{\text{DD0}} < 5.5 \text{ V},$ $\text{IoL1} = 0.3 \text{ mA}$			0.4	V
	V _{OL2}	P20 to P27, P150 to P156	1.6 V \leq V _{DD} \leq 5.5 V, I _{OL2} = 400 μ A			0.4	V
	Vol3	P60 to P63	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $\text{Iol3} = 15.0 \text{ mA}$			2.0	V
			$4.0~V \le EV_{DD0} \le 5.5~V,$ $I_{OL3} = 5.0~mA$			0.4	V
			$2.7~\textrm{V} \leq \textrm{EV}_\textrm{DD0} \leq 5.5~\textrm{V},$ $\textrm{Iol3} = 3.0~\textrm{mA}$			0.4	V
			$1.8~V \leq EV_{DD0} \leq 5.5~V,$ $I_{OL3} = 2.0~mA$			0.4	V
			$1.6 \text{ V} \le \text{EV}_{\text{DD0}} < 5.5 \text{ V},$ $10 \text{L3} = 1.0 \text{ mA}$			0.4	V

Caution P00, P02 to P04, P10 to P15, P17, P43 to P45, P50, P52 to P55, P71, P74, P80 to P82, P96, and P142 to P144 do not output high level in N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

(2) During communication at same potential (CSI mode) (master mode, SCKp... internal clock output, corresponding CSI00 only)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 2.7 \text{ V} \le \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0 \text{ V})$

Parameter	Symbol	(Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low- main)	-voltage Mode	Unit
					MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	t KCY1	tkcy1 ≥ 2/fclk	$4.0~V \leq EV_{DD0} \leq 5.5~V$	62.5		250		500		ns
			$2.7~V \leq EV_{DD0} \leq 5.5~V$	83.3		250		500		ns
SCKp high-/low-level width	tкн1, tкL1	4.0 V ≤ EV _{DI}	oo ≤ 5.5 V	tксү1/2 — 7		tксү1/2 – 50		tксү1/2 — 50		ns
		2.7 V ≤ EV _{DI}	2.7 V ≤ EV _{DD0} ≤ 5.5 V			tксү1/2 – 50		tксү1/2 — 50		ns
SIp setup time (to SCKp↑)	tsıĸı	4.0 V ≤ EV _{DI}	4.0 V ≤ EV _{DD0} ≤ 5.5 V			110		110		ns
Note 1		2.7 V ≤ EV _{DI}	00 ≤ 5.5 V	33		110		110		ns
SIp hold time (from SCKp↑) Note 2	tksı1	2.7 V ≤ EV _{DI}	2.7 V ≤ EV _{DD0} ≤ 5.5 V			10		10		ns
Delay time from SCKp↓ to SOp output Note 3	tkso1	C = 20 pF No	te 4		10		10		10	ns

- **Notes 1.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 4. C is the load capacitance of the SCKp and SOp output lines.

Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

- Remarks 1. This value is valid only when CSI00's peripheral I/O redirect function is not used.
 - p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0),g: PIM and POM numbers (g = 1)
 - 3. fmck: Serial array unit operation clock frequency(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,n: Channel number (mn = 00))

Remarks 1. p: CSI number (p = 00, 01, 10, 11, 20, 21, 30, 31), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3),

g: PIM and POM numbers (g = 0, 1, 4, 5, 8, 14)

2. fmck: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

n: Channel number (mn = 00 to 03, 10 to 13))

(4) During communication at same potential (CSI mode) (slave mode, SCKp... external clock input) (1/2)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$

Parameter	Symbol	Condit		HS (hig	h-speed Mode	LS (low	r-speed Mode	LV (low main)	-voltage Mode	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	tkcy2	$4.0~V \leq EV_{DD0} \leq 5.5$	20 MHz < fмск	8/fмск				_		ns
Note 5		V	fмcк ≤ 20 MHz	6/fмск		6/ƒмск		6/ƒмск		ns
		$2.7~V \leq EV_{DD0} \leq 5.5$	16 MHz < fмск	8/fмск		_		_		ns
		V	fмcк ≤ 16 MHz	6/fмск		6/fмск		6/fмск		ns
		$2.4~V \le EV_{DD0} \le 5.5~V$		6/fмск and 500		6/fмск and 500		6/fмск and 500		ns
		1.8 V ≤ EV _{DD0} ≤ 5.5 V		6/fмск and 750		6/fмск and 750		6/fмск and 750		ns
		1.7 V ≤ EV _{DD0} ≤ 5.5 V		6/fмск and 1500		6/fмск and 1500		6/fмск and 1500		ns
		1.6 V ≤ EV _{DD0} ≤ 5.5	V	_		6/fмск and 1500		6/fмск and 1500		ns
SCKp high-/low- level width	tkH2,	4.0 V ≤ EV _{DD0} ≤ 5.5 V		tксү2/2 – 7		tксү2/2 - 7		tксү2/2 - 7		ns
		$2.7~\text{V} \leq \text{EV}_\text{DD0} \leq 5.5~\text{V}$		tксу2/2 — 8		tксу2/2 - 8		tксу2/2 - 8		ns
		1.8 V ≤ EV _{DD0} ≤ 5.5 V		tксү2/2 – 18		tксу2/2 - 18		tксу2/2 - 18		ns
		1.7 V ≤ EV _{DD0} ≤ 5.5 V		tксү2/2 – 66		tксү2/2 - 66		tксү2/2 - 66		ns
		1.6 V ≤ EV _{DD0} ≤ 5.5	V	_		tkcy2/2 - 66		tkcy2/2 - 66		ns

(Notes, Caution, and Remarks are listed on the next page.)

(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (1/2)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$

Parameter	Symbol		Conditions		speed	high- I main) ode		/-speed Mode	voltage	low- e main) ode	Unit
					MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Transfer rate		Recep- tion	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V}$			fMCK/6 Note 1		fMCK/6 Note 1		fMCK/6 Note 1	bps
				Theoretical value of the maximum transfer rate fmck = fclk Note 4		5.3		1.3		0.6	Mbps
			$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V}$			fMCK/6 Note 1		fMCK/6 Note 1		fMCK/6 Note 1	bps
				Theoretical value of the maximum transfer rate folk Note 4		5.3		1.3		0.6	Mbps
			$1.8 \ V \le EV_{DD0} < 3.3 \ V,$ $1.6 \ V \le V_b \le 2.0 \ V$			fMCK/6 Notes 1 to 3		fMCK/6 Notes 1, 2		fMCK/6 Notes 1, 2	bps
				Theoretical value of the maximum transfer rate fmck = fclk Note 4		5.3		1.3		0.6	Mbps

Notes 1. Transfer rate in the SNOOZE mode is 4800 bps only.

- 2. Use it with EVDD0≥Vb.
- 3. The following conditions are required for low voltage interface when $E_{VDDO} < V_{DD}$.

 $2.4 \text{ V} \le \text{EV}_{\text{DD0}} < 2.7 \text{ V} : \text{MAX. } 2.6 \text{ Mbps}$ $1.8 \text{ V} \le \text{EV}_{\text{DD0}} < 2.4 \text{ V} : \text{MAX. } 1.3 \text{ Mbps}$

4. The maximum operating frequencies of the CPU/peripheral hardware clock (fclk) are:

HS (high-speed main) mode: 32 MHz (2.7 V \leq V_{DD} \leq 5.5 V)

16 MHz (2.4 V \leq V_{DD} \leq 5.5 V)

LS (low-speed main) mode: 8 MHz (1.8 V \leq V_{DD} \leq 5.5 V) LV (low-voltage main) mode: 4 MHz (1.6 V \leq V_{DD} \leq 5.5 V)

Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (Vpd tolerance (When 20- to 52-pin products)/EVpd tolerance (When 64- to 128-pin products)) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For ViH and ViL, see the DC characteristics with TTL input buffer selected.

Remarks 1. $V_b[V]$: Communication line voltage

- **2.** q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 8, 14)
- 3. fmcκ: Serial array unit operation clock frequency(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,n: Channel number (mn = 00 to 03, 10 to 13)
- **4.** UART2 cannot communicate at different potential when bit 1 (PIOR1) of peripheral I/O redirection register (PIOR) is 1.

(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (2/2)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$

Parameter	Symbol	Conditions		HS (high-	LS (low-		low- age Mode	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Transfer rate		$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V}$			Note 1		Note 1		Note 1	bps
			Theoretical value of the maximum transfer rate $C_b = 50 \text{ pF}, R_b = 1.4 \text{ k}\Omega, V_b = 2.7 \text{ V}$		2.8 Note 2		2.8 Note 2		2.8 Note 2	Mbps
		$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V}$			Note 3		Note 3		Note 3	bps
		2.3 V ≤ Vb ≤ 2.7 V	Theoretical value of the maximum transfer rate Cb = 50 pF, Rb =		1.2 Note 4		1.2 Note 4		1.2 Note 4	Mbps
			$2.7 \text{ k}\Omega, V_b = 2.3$							
		$1.8 \ V \le EV_{DD0} < 3.3 \ V,$ $1.6 \ V \le V_b \le 2.0 \ V$			Notes 5, 6		Notes 5, 6		Notes 5, 6	bps
			Theoretical value of the maximum transfer rate		0.43 Note 7		0.43 Note 7		0.43 Note 7	Mbps
			$C_b = 50 \text{ pF}, R_b = 5.5 \text{ k}\Omega, V_b = 1.6 \text{ V}$							

Notes 1. The smaller maximum transfer rate derived by using fmck/6 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 4.0 V \leq EV $_{DD0} \leq$ 5.5 V and 2.7 V \leq V $_{b} \leq$ 4.0 V

Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{2.2}{V_b})\} \times 3}$$
 [bps]

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln{(1 - \frac{2.2}{V_b})}\}}{\frac{1}{(\text{Transfer rate})} \times \text{Number of transferred bits}} \times 100 \, [\%]$$

- * This value is the theoretical value of the relative difference between the transmission and reception sides.
- 2. This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 1 above to calculate the maximum transfer rate under conditions of the customer.



(7) Communication at different potential (2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output, corresponding CSI00 only) (1/2)

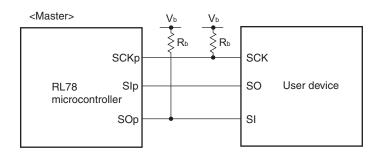
(Ta = -40 to +85°C, 2.7 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, Vss = EVss0 = EVss1 = 0 V)

Parameter	Symbol		Conditions	HS (hig	h-speed Mode	LS (low		LV (low- main)	-	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	tkcy1	tkcy1 ≥ 2/fclk	$\begin{aligned} 4.0 & \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}, \\ 2.7 & \text{ V} \leq \text{V}_{\text{b}} \leq 4.0 \text{ V}, \\ C_{\text{b}} = 20 \text{ pF}, R_{\text{b}} = 1.4 \\ k\Omega \end{aligned}$	200		1150		1150		ns
			$\begin{split} &2.7 \text{ V} \leq \text{EV}_{\text{DD0}} < 4.0 \text{ V}, \\ &2.3 \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V}, \\ &C_{\text{b}} = 20 \text{ pF}, R_{\text{b}} = 2.7 \\ &k\Omega \end{split}$	300		1150		1150		ns
SCKp high-level width	tкн1	$4.0 \text{ V} \leq \text{EV}_{DD}$ $2.7 \text{ V} \leq \text{V}_{b} \leq 6$ $C_{b} = 20 \text{ pF, F}$	4.0 V,	tксү1/2 — 50		tксу1/2 — 50		tксу1/2 — 50		ns
		$2.7 \text{ V} \leq \text{EV}_{DD}$ $2.3 \text{ V} \leq \text{V}_{b} \leq 2.2 \text{ C}$ $C_{b} = 20 \text{ pF}, \text{ F}$	2.7 V,	tксү1/2 — 120		tксу1/2 – 120		tксу1/2 — 120		ns
SCKp low-level width	t _{KL1}	$4.0 \text{ V} \leq \text{EV}_{DD}$ $2.7 \text{ V} \leq \text{V}_{b} \leq 6$ $C_{b} = 20 \text{ pF, F}$	4.0 V,	tксү1/2 — 7		t _{KCY1} /2 – 50		t _{KCY1} /2 – 50		ns
		$2.7 \text{ V} \leq \text{EV}_{DD}$ $2.3 \text{ V} \leq \text{V}_{b} \leq 2$ $C_{b} = 20 \text{ pF, F}$	2.7 V,	tксу ₁ /2 – 10		tксу1/2 — 50		tксу1/2 — 50		ns
SIp setup time (to SCKp↑) Note 1	tsıĸı	$4.0 \text{ V} \leq \text{EV}_{DD}$ $2.7 \text{ V} \leq \text{V}_{b} \leq 4$ $C_{b} = 20 \text{ pF, F}$	4.0 V,	58		479		479		ns
		$2.7 \text{ V} \leq \text{EV}_{DD}$ $2.3 \text{ V} \leq \text{V}_{b} \leq 2$ $C_{b} = 20 \text{ pF, F}$	2.7 V,	121		479		479		ns
SIp hold time (from SCKp↑) Note 1	tksii	$4.0 \text{ V} \leq \text{EV}_{DD}$ $2.7 \text{ V} \leq \text{V}_{b} \leq 6$ $C_{b} = 20 \text{ pF, F}$	4.0 V,	10		10		10		ns
		$2.7 \text{ V} \leq \text{EV}_{DD}$ $2.3 \text{ V} \leq \text{V}_{b} \leq 2$ $C_{b} = 20 \text{ pF, F}$	2.7 V,	10		10		10		ns
Delay time from SCKp↓ to SOp output Note 1	tkso1	$4.0 \text{ V} \le \text{EV}_{DD}$ $2.7 \text{ V} \le \text{V}_{b} \le 6$ $C_{b} = 20 \text{ pF, F}$	4.0 V,		60		60		60	ns
		$2.7 \text{ V} \le \text{EV}_{DD}$ $2.3 \text{ V} \le \text{V}_{b} \le 2$ $C_b = 20 \text{ pF, F}$	o < 4.0 V, 2.7 V,		130		130		130	ns

(Notes, Caution, and Remarks are listed on the next page.)



CSI mode connection diagram (during communication at different potential)



- **Remarks 1.** R_b[Ω]:Communication line (SCKp, SOp) pull-up resistance, C_b[F]: Communication line (SCKp, SOp) load capacitance, V_b[V]: Communication line voltage
 - **2.** p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number , n: Channel number (mn = 00, 01, 02, 10, 12, 13), g: PIM and POM number (g = 0, 1, 4, 5, 8, 14)
 - 3. fmck: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00))
 - **4.** CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.

(10) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I²C mode) (2/2)

(Ta = -40 to +85°C, 1.8 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, Vss = EVss0 = EVss1 = 0 V)

Parameter	Symbol	Conditions	HS (high	•	`	/-speed Mode	LV (low main)	-voltage Mode	Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Data setup time (reception)	tsu:dat	$\begin{aligned} &4.0 \; V \leq EV_{DD0} \leq 5.5 \; V, \\ &2.7 \; V \leq V_b \leq 4.0 \; V, \\ &C_b = 50 \; pF, \; R_b = 2.7 \; k\Omega \end{aligned}$	1/f _{MCK} + 135 Note 3		1/fmck + 190 Note 3		1/fmck + 190 Note 3		kHz
		$\label{eq:substitute} \begin{split} 2.7 \ V &\leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V &\leq V_b \leq 2.7 \ V, \\ C_b &= 50 \ pF, \ R_b = 2.7 \ k\Omega \end{split}$	1/f _{MCK} + 135 Note 3		1/fmck + 190 Note 3		1/fmck + 190 Note 3		kHz
		$ \begin{aligned} &4.0 \; V \leq EV_{DD0} \leq 5.5 \; V, \\ &2.7 \; V \leq V_b \leq 4.0 \; V, \\ &C_b = 100 \; pF, \; R_b = 2.8 \; k\Omega \end{aligned} $	1/f _{MCK} + 190 Note 3		1/fmck + 190 Note 3		1/fmck + 190 Note 3		kHz
		$\label{eq:section} \begin{split} 2.7 \ V &\leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V &\leq V_b \leq 2.7 \ V, \\ C_b &= 100 \ pF, \ R_b = 2.7 \ k\Omega \end{split}$	1/f _{MCK} + 190 Note 3		1/fMCK + 190 Note 3		1/fmck + 190 Note 3		kHz
		$ \begin{aligned} &1.8 \; V \leq EV_{DD0} < 3.3 \; V, \\ &1.6 \; V \leq V_b \leq 2.0 \; V^{\text{Note 2}}, \\ &C_b = 100 \; pF, \; R_b = 5.5 \; k\Omega \end{aligned} $	1/f _{MCK} + 190 Note 3		1/fMCK + 190 Note 3		1/fmck + 190 Note 3		kHz
Data hold time (transmission)	thd:dat	$ \begin{aligned} &4.0 \; V \leq EV_{DD0} \leq 5.5 \; V, \\ &2.7 \; V \leq V_b \leq 4.0 \; V, \\ &C_b = 50 \; pF, \; R_b = 2.7 \; k\Omega \end{aligned} $	0	305	0	305	0	305	ns
		$ \begin{aligned} &2.7 \; V \leq EV_{DD0} < 4.0 \; V, \\ &2.3 \; V \leq V_b \leq 2.7 \; V, \\ &C_b = 50 \; pF, \; R_b = 2.7 \; k\Omega \end{aligned} $	0	305	0	305	0	305	ns
		$ \begin{cases} 4.0 \; V \leq EV_{DD0} \leq 5.5 \; V, \\ 2.7 \; V \leq V_b \leq 4.0 \; V, \\ C_b = 100 \; pF, \; R_b = 2.8 \; k\Omega \end{cases} $	0	355	0	355	0	355	ns
		eq:second-seco	0	355	0	355	0	355	ns
		$\begin{split} &1.8 \; V \leq EV_{DD0} < 3.3 \; V, \\ &1.6 \; V \leq V_b \leq 2.0 \; V^{\text{Note 2}}, \\ &C_b = 100 \; pF, \; R_b = 5.5 \; k\Omega \end{split}$	0	405	0	405	0	405	ns

Notes 1. The value must also be equal to or less than $f_{MCK}/4$.

- 2. Use it with $EV_{DD0} \ge V_b$.
- 3. Set the fmck value to keep the hold time of SCLr = "L" and SCLr = "H".

Caution Select the TTL input buffer and the N-ch open drain output (VDD tolerance (for the 20- to 52-pin products)/EVDD tolerance (for the 64- to 128-pin products)) mode for the SDAr pin and the N-ch open drain output (VDD tolerance (for the 20- to 52-pin products)/EVDD tolerance (for the 64- to 128-pin products)) mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

(Remarks are listed on the next page.)

3.4 AC Characteristics

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$

Items	Symbol		MIN.	TYP.	MAX.	Unit		
Instruction cycle (minimum	Tcy	Main	HS (high-speed	$1 2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}$	0.03125		1	μS
instruction execution time)		system clock (fmain) operation	main) mode	$2.4 \text{ V} \le \text{V}_{DD} < 2.7 \text{ V}$	0.0625		1	μS
		Subsystem of operation	clock (fsua)	$2.4~V \le V_{DD} \le 5.5~V$	28.5	30.5	31.3	μS
		In the self	HS (high-speed	$1 2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}$	0.03125		1	μS
		programming mode	main) mode	$2.4 \text{ V} \le \text{V}_{DD} < 2.7 \text{ V}$	0.0625		1	μS
External system clock frequency	fex	$2.7 \text{ V} \leq \text{V}_{DD} \leq$	≤ 5.5 V		1.0		20.0	MHz
		2.4 V ≤ V _{DD} <	< 2.7 V		1.0		16.0	MHz
	fexs				32		35	kHz
External system clock input high-	texh, texl	2.7 V ≤ V _{DD} ≤	≤ 5.5 V		24			ns
level width, low-level width		2.4 V ≤ V _{DD} <	< 2.7 V		30			ns
	texhs, texhs				13.7			μS
TI00 to TI07, TI10 to TI17 input high-level width, low-level width	tтін, tтіL				1/fмск+10			ns ^{Note}
TO00 to TO07, TO10 to TO17	f то	HS (high-spe	eed 4.0 V	≤ EV _{DD0} ≤ 5.5 V			16	MHz
output frequency		main) mode	2.7 V	≤ EV _{DD0} < 4.0 V			8	MHz
			2.4 V	≤ EV _{DD0} < 2.7 V			4	MHz
PCLBUZ0, PCLBUZ1 output	fpcL	HS (high-spe	eed 4.0 V	≤ EV _{DD0} ≤ 5.5 V			16	MHz
frequency		main) mode	2.7 V	≤ EV _{DD0} < 4.0 V			8	MHz
			2.4 V	≤ EV _{DD0} < 2.7 V			4	MHz
Interrupt input high-level width,	tinth,	INTP0	2.4 V	$\leq V_{DD} \leq 5.5 \text{ V}$	1			μS
low-level width	tintl	INTP1 to INT	TP11 2.4 V	$\leq EV_{DD0} \leq 5.5 V$	1			μS
Key interrupt input low-level width	t KR	KR0 to KR7	2.4 V	$\leq EV_{DD0} \leq 5.5 \text{ V}$	250			ns
RESET low-level width	trsL		•		10			μS

Note The following conditions are required for low voltage interface when $E_{VDD0} < V_{DD}$ $2.4V \le EV_{DD0} < 2.7 \text{ V}$: MIN. 125 ns

Remark fmck: Timer array unit operation clock frequency

(Operation clock to be set by the CKSmn0, CKSmn1 bits of timer mode register mn (TMRmn).

m: Unit number (m = 0, 1), n: Channel number (n = 0 to 7))

(7) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (slave mode, SCKp... external clock input)

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0 \text{ V})$

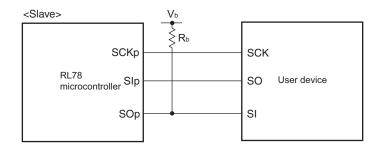
Parameter	Symbol	Conditions		HS (high-spe	Unit	
				MIN.	MAX.	
SCKp cycle time Note 1	tkcy2	$4.0~V \leq EV_{DD0} \leq 5.5$	24 MHz < fмск	28/fмск		ns
		$V,$ $2.7~V \leq V_b \leq 4.0~V$	20 MHz < fмcк ≤ 24 MHz	24/fмск		ns
			8 MHz < fмck ≤ 20 MHz	20/fмск		ns
			4 MHz < fmck ≤ 8 MHz	16/fмск		ns
			fмcк ≤ 4 MHz	12/fмск		ns
		$2.7 \text{ V} \le \text{EV}_{\text{DDO}} < 4.0 \text{ V},$	24 MHz < fмск	40/fмск		ns
			$20~\text{MHz} < \text{fmck} \le 24~\text{MHz}$	32/fмск		ns
		$2.3 \ V \leq V_b \leq 2.7 \ V$	16 MHz < fмcк ≤ 20 MHz	28/fмск		ns
			8 MHz < fмcк ≤ 16 MHz	24/fмск		ns
			4 MHz < fмcк ≤ 8 MHz	16/fмск		ns
			fмcк ≤ 4 MHz	12/fмск		ns
		2.4 V ≤ EV _{DD0} < 3.3	24 MHz < fмск	96/fмск		ns
		V,	20 MHz < fмcк ≤ 24 MHz	72/fмск		ns
		$1.6~V \leq V_b \leq 2.0~V$	16 MHz < fмcк ≤ 20 MHz	64/fмск		ns
			8 MHz < fмcк ≤ 16 MHz	52/fмск		ns
			4 MHz < fмcк ≤ 8 MHz	32/fмск		ns
			fмcк ≤ 4 MHz	20/fмск		ns
SCKp high-/low-level width	tкн2, tкL2	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V}$		tксу2/2 - 24		ns
Slp setup time (to SCKp [↑]) Note2		$2.7 \ V \le EV_{DD0} < 4.$ $2.3 \ V \le V_b \le 2.7 \ V$		tkcy2/2 - 36		ns
		$2.4 \ V \le EV_{DD0} < 3.$ $1.6 \ V \le V_b \le 2.0 \ V$		tkcy2/2 - 100		ns
	tsık2	$ 4.0 \ V \leq EV_{DD0} \leq 5.5 $ $ 2.7 \ V \leq V_b \leq 4.0 \ V $	5 V,	1/fмск + 40		ns
		$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V}$		1/fмск + 40		ns
		$2.4 \ V \le EV_{DD0} < 3.$ $1.6 \ V \le V_b \le 2.0 \ V$	3 V,	1/fмск + 60		ns
Slp hold time (from SCKp [↑]) Note 3	tksi2			1/fmck + 62		ns
Delay time from SCKp↓ to SOp output Note 4	t kso2	$4.0~V \leq EV_{DD0} \leq 5.$ $C_b = 30~pF,~R_b = 1$	5 V, 2.7 V \leq V _b \leq 4.0 V, .4 k Ω		2/fмск + 240	ns
		$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.$ $C_{\text{b}} = 30 \text{ pF}, R_{\text{b}} = 2$	0 V, 2.3 V \leq V _b \leq 2.7 V, .7 kΩ		2/fмск + 428	ns
		$2.4 \ V \le EV_{DD0} < 3.$ $C_b = 30 \ pF, \ R_b = 5$	3 V, 1.6 V ≤ V _b ≤ 2.0 V .5 kΩ		2/fмск + 1146	ns

(Notes, Caution and Remarks are listed on the next page.)

- Notes 1. Transfer rate in the SNOOZE mode: MAX. 1 Mbps
 - 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - **4.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Caution Select the TTL input buffer for the SIp pin and SCKp pin and the N-ch open drain output (VDD tolerance (for the 20- to 52-pin products)/EVDD tolerance (for the 64- to 128-pin products)) mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VH and VIL, see the DC characteristics with TTL input buffer selected.

CSI mode connection diagram (during communication at different potential)



- **Remarks 1.** R_b[Ω]:Communication line (SOp) pull-up resistance, C_b[F]: Communication line (SOp) load capacitance, V_b[V]: Communication line voltage
 - 2. p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number (m = 0, 1), n: Channel number (n = 00, 01, 02,
 - 10, 12, 13), g: PIM and POM number (g = 0, 1, 4, 5, 8, 14)
 - 3. fmck: Serial array unit operation clock frequency(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn).m: Unit number, n: Channel number (mn = 00, 01, 02, 10, 12, 13))
 - **4.** CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.

(4) When reference voltage (+) = Internal reference voltage (ADREFP1 = 1, ADREFP0 = 0), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin : ANI0, ANI2 to ANI14, ANI16 to ANI26

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{\text{DD}0} = \text{EV}_{\text{DD}1} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{V}_{\text{SS}} = \text{EV}_{\text{SS}0} = \text{EV}_{\text{SS}1} = 0 \text{ V}, \text{Reference voltage (+)} = \text{V}_{\text{BGR}}^{\text{Note 3}}, \text{Reference voltage (-)} = \text{AV}_{\text{REFM}}^{\text{Note 4}} = 0 \text{ V}, \text{HS (high-speed main) mode)}$

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES				8		bit
Conversion time	tconv	8-bit resolution	$2.4~V \leq V_{DD} \leq 5.5~V$	17		39	μS
Zero-scale error ^{Notes 1, 2}	Ezs	8-bit resolution	$2.4~V \leq V_{DD} \leq 5.5~V$			±0.60	%FSR
Integral linearity error ^{Note 1}	ILE	8-bit resolution	$2.4~V \leq V_{DD} \leq 5.5~V$			±2.0	LSB
Differential linearity error Note 1	DLE	8-bit resolution	$2.4~V \leq V_{DD} \leq 5.5~V$			±1.0	LSB
Analog input voltage	Vain			0		V _{BGR} Note 3	V

- **Notes 1.** Excludes quantization error ($\pm 1/2$ LSB).
 - 2. This value is indicated as a ratio (%FSR) to the full-scale value.
 - 3. Refer to 3.6.2 Temperature sensor/internal reference voltage characteristics.
 - 4. When reference voltage (-) = Vss, the MAX. values are as follows.
 Zero-scale error: Add ±0.35%FSR to the MAX. value when reference voltage (-) = AVREFM.
 Integral linearity error: Add ±0.5 LSB to the MAX. value when reference voltage (-) = AVREFM.
 Differential linearity error: Add ±0.2 LSB to the MAX. value when reference voltage (-) = AVREFM.

3.6.2 Temperature sensor/internal reference voltage characteristics

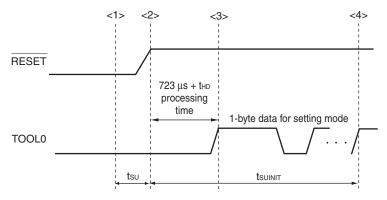
(TA = -40 to +105°C, 2.4 V \leq VDD \leq 5.5 V, Vss = 0 V, HS (high-speed main) mode)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Temperature sensor output voltage	V _{TMPS25}	Setting ADS register = 80H, Ta = +25°C		1.05		V
Internal reference voltage	V _{BGR}	Setting ADS register = 81H	1.38	1.45	1.5	٧
Temperature coefficient	Fvтмps	Temperature sensor that depends on the temperature		-3.6		mV/°C
Operation stabilization wait time	tamp		5			μS

3.10 Timing of Entry to Flash Memory Programming Modes

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Time to complete the communication for the initial setting after the external reset is released	tsuinit	POR and LVD reset must be released before the external reset is released.			100	ms
Time to release the external reset after the TOOL0 pin is set to the low level	tsu	POR and LVD reset must be released before the external reset is released.	10			μS
Time to hold the TOOL0 pin at the low level after the external reset is released (excluding the processing time of the firmware to control the flash memory)		POR and LVD reset must be released before the external reset is released.	1			ms



- <1> The low level is input to the TOOL0 pin.
- <2> The external reset is released (POR and LVD reset must be released before the external reset is released.).
- <3> The TOOL0 pin is set to the high level.
- <4> Setting of the flash memory programming mode by UART reception and complete the baud rate setting.

Remark tsuinit: Communication for the initial setting must be completed within 100 ms after the external reset is released during this period.

tsu: Time to release the external reset after the TOOL0 pin is set to the low level

thd: Time to hold the TOOL0 pin at the low level after the external reset is released (excluding the processing time of the firmware to control the flash memory)

4.9 48-pin Products

R5F100GAAFB, R5F100GCAFB, R5F100GDAFB, R5F100GEAFB, R5F100GFAFB, R5F100GAFB, R5F100GHAFB, R5F100GJAFB, R5F100GKAFB, R5F100GLAFB

R5F101GAAFB, R5F101GCAFB, R5F101GDAFB, R5F101GEAFB, R5F101GFAFB, R5F101GHAFB, R5F101GJAFB, R5F101GKAFB, R5F101GLAFB

R5F100GADFB, R5F100GCDFB, R5F100GDDFB, R5F100GEDFB, R5F100GFDFB, R5F100GHDFB, R5F100GHDFB, R5F100GHDFB, R5F100GHDFB, R5F100GHDFB

R5F101GADFB, R5F101GCDFB, R5F101GDDFB, R5F101GEDFB, R5F101GFDFB, R5F101GHDFB, R5F101GJDFB, R5F101GKDFB, R5F101GKDFB, R5F101GKDFB, R5F101GKDFB

R5F100GAGFB, R5F100GCGFB, R5F100GDGFB, R5F100GEGFB, R5F100GFGFB, R5F100GHGFB, R5F10

Γ	JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.)	[g]
	P-LFQFP48-7x7-0.50	PLQP0048KF-A	P48GA-50-8EU-1	0.16	
	HD— 36 37	25 24	F E HE	detail of I	C — L Lp
	48	13			(UNIT:mm)
	. 1	12.	ļ	ITEM	DIMENSIONS
				D	7.00±0.20
-ZE				E	7.00±0.20
		J W W U U	<u>v</u> _	HD	9.00±0.20
				HE	9.00±0.20
	ZD	е		HE A	9.00±0.20 1.60 MAX.
				HE A A1	9.00±0.20 1.60 MAX. 0.10±0.05
			А¬	HE A A1 A2	9.00±0.20 1.60 MAX. 0.10±0.05 1.40±0.05
			A 7 A2 7	HE A A1 A2 A3	9.00±0.20 1.60 MAX. 0.10±0.05 1.40±0.05 0.25
				HE A A1 A2 A3 b	9.00±0.20 1.60 MAX. 0.10±0.05 1.40±0.05 0.25 0.22±0.05
				HE A A1 A2 A3 b	9.00±0.20 1.60 MAX. 0.10±0.05 1.40±0.05 0.25
				HE A A1 A2 A3 b c	9.00±0.20 1.60 MAX. 0.10±0.05 1.40±0.05 0.25 0.22±0.05 0.145 +0.055 0.50
				HE A A1 A2 A3 b C L Lp	9.00±0.20 1.60 MAX. 0.10±0.05 1.40±0.05 0.25 0.22±0.05 0.145 +0.055 0.50 0.60±0.15
				HE A A1 A2 A3 b C L Lp L1	9.00±0.20 1.60 MAX. 0.10±0.05 1.40±0.05 0.25 0.22±0.05 0.145 +0.055 0.50 0.60±0.15 1.00±0.20
	- b ()		A2 -	HE A A1 A2 A3 b C L Lp	9.00±0.20 1.60 MAX. 0.10±0.05 1.40±0.05 0.25 0.22±0.05 0.145 +0.055 0.50 0.60±0.15
				HE A A1 A2 A3 b C L Lp L1	9.00±0.20 1.60 MAX. 0.10±0.05 1.40±0.05 0.25 0.22±0.05 0.145 +0.055 0.50 0.60±0.15 1.00±0.20
	- b ()		A2 -	HE A A1 A2 A3 b c L Lp L1 θ	9.00±0.20 1.60 MAX. 0.10±0.05 1.40±0.05 0.25 0.22±0.05 0.145 +0.055 0.50 0.60±0.15 1.00±0.20 3°+5°

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ZD

ZE

0.75

0.75

Each lead centerline is located within 0.08 mm of its true position at maximum material condition.

			Description
Rev.	Date	Page	Summary
3.00	3.00 Aug 02, 2013	118	Modification of table in 2.6.2 Temperature sensor/internal reference voltage characteristics
		118	Modification of table and note in 2.6.3 POR circuit characteristics
		119	Modification of table in 2.6.4 LVD circuit characteristics
		120	Modification of table of LVD Detection Voltage of Interrupt & Reset Mode
		120	Renamed to 2.6.5 Power supply voltage rising slope characteristics
		122	Modification of table, figure, and remark in 2.10 Timing Specs for Switching Flash Memory Programming Modes
		123	Modification of caution 1 and description
		124	Modification of table and remark 3 in Absolute Maximum Ratings (T _A = 25°C)
		126	Modification of table, note, caution, and remark in 3.2.1 X1, XT1 oscillator characteristics
		126	Modification of table in 3.2.2 On-chip oscillator characteristics
		127	Modification of note 3 in 3.3.1 Pin characteristics (1/5)
		128	Modification of note 3 in 3.3.1 Pin characteristics (2/5)
		133	Modification of notes 1 and 4 in (1) Flash ROM: 16 to 64 KB of 20- to 64-pin products (1/2)
		135	Modification of notes 1, 5, and 6 in (1) Flash ROM: 16 to 64 KB of 20- to 64-pin products (2/2)
		137	Modification of notes 1 and 4 in (2) Flash ROM: 96 to 256 KB of 30- to 100-pin products (1/2)
		139	Modification of notes 1, 5, and 6 in (2) Flash ROM: 96 to 256 KB of 30- to 100-pin products (2/2)
		140	Modification of (3) Peripheral Functions (Common to all products)
		142	Modification of table in 3.4 AC Characteristics
		143	Addition of Minimum Instruction Execution Time during Main System Clock Operation
		143	Modification of figure of AC Timing Test Points
		143	Modification of figure of External System Clock Timing
		145	Modification of figure of AC Timing Test Points
		145	Modification of description, note 1, and caution in (1) During communication at same potential (UART mode)
		146	Modification of description in (2) During communication at same potential (CSI mode)
		147	Modification of description in (3) During communication at same potential (CSI mode)
		149	Modification of table, note 1, and caution in (4) During communication at same potential (simplified I ² C mode)
		151	Modification of table, note 1, and caution in (5) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (1/2)
		152 to 154	Modification of table, notes 2 to 6, caution, and remarks 1 to 4 in (5) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (2/2)
		155	Modification of table in (6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (1/3)
		156	Modification of table and caution in (6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (2/3)
		157, 158	Modification of table, caution, and remarks 3 and 4 in (6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (3/3)
		160, 161	Modification of table and caution in (7) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode)